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Page: 1/3

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[Title of the Invention] SEMICONDUCTOR DEVICE AND MANUFACTURING

METHOD THEREOF

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Page: 3/3

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Page: 1/32

[Document Name] Specification

[Title of the Invention] SEMICONDUCTOR DEVICE AND MANUFACTURING

METHOD THEREOF

[Claims]

1. A semiconductor device, comprising:

a semiconductor substrate,

an element formation region placed in a portion of the substrate,

groove-type element isolation that surrounds the element formation region, and that comprises a height difference part, which becomes higher in a step manner than the semiconductor substrate of the element formation region, with the element formation region, and that is made from an insulating material, and

height difference-part sidewalls formed on side surfaces of the height difference part between the element formation region and the groove-type element isolation.

- 2. The semiconductor device according to claim 1, wherein the height difference-part sidewalls are formed with an insulating material.
- 3. The semiconductor device according to claim 1, wherein

a MISFET, comprising: a gate electrode and electrode-part sidewalls on both side surfaces of the gate electrode is formed in the element formation region, and

the height difference-part sidewalls are formed at the same time as the electrode-part sidewalls.

4. The substrate device according to claim 3,

the electrode-part sidewalls are formed with an L-shaped silicon nitride film with substantially constant thickness that is formed via a protective oxide film throughout the side surfaces of the gate electrode onto the semiconductor substrate; and

the height difference-part sidewalls are formed with an L-shaped silicon nitride film with substantially constant thickness that are formed via a protective oxide film throughout side surfaces between the element formation region and the groove-type element isolation onto the semiconductor substrate.



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